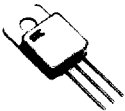
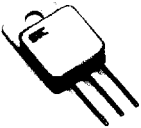
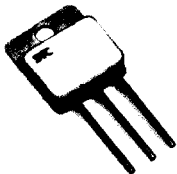


IGBT

IGBT: INS. GATE BIPOLAR TRANSISTOR

PACKAGE	DEVICE TYPE	V_{CES} VOLTS	I_C (cont) AMPS	V_{CE} (sat) VOLTS	t_f (1) nsec*	C_{ies} pf	θ_{JC} c/w
T0-257 	SNG30620	600	20	2.6	570	750	2.0
	SNG30620A	600	20	3.1	310	750	2.0
T0-254 	SNG20640	600 @ 90° c	31	2.0	800	1500	1.25
	SNG20648A	600 @ 90° c	24	2.9	100	1500	1.25
	SNG21034	1000	34	3.6	750	1500	1.25
T0-258 	SNG40635	600	35	2.7	250	1200	1.10
	SNG40640	600	40	2.0	800	1500	1.0
	SNG40648A	600	48	2.9	100	1500	1.0
	SNG40660A	600	60	3.1	125	2500	0.85
	SNG40675	600	75	2.0	400	4000	0.75
	SNG40675A	600	75	2.9	175	4000	0.75
	SNG41045	1000	45	3.2	300	2100	0.75
	SNG41065	1000	65	3.2	300	3500	0.75
	SNG41270A	1200	70	4.2	500	4300	0.75
	SNG41275A	1200	75	3.2	1200	4300	0.75

• Electrical Characteristics at 25° C unless otherwise noted

* Typical

(1) t_f is a function of RG